

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

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Claims 1-8 (Canceled)

Claim ~~9~~<sup>1</sup> (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a first insulation film on a patterned conductive layer on a substrate,

[introducing] implanting impurities into and penetrating through said first insulation film,

and

forming an intrusion prevention film to selectively cover said conductive layer and to substantially prevent the impurities [introduced into] implanted through said first insulation film from entering said conductive layer prior to said step of forming said first insulation film.

Claim ~~10~~<sup>2</sup> (Original) The manufacturing method of a semiconductor device according to claim ~~9~~<sup>1</sup>, wherein said intrusion prevention film includes at least one material selected from the group consisting of silicon oxide, silicon nitride, Ti, TiN, W, WN<sub>x</sub> and TiW.

Claim ~~11~~<sup>3</sup> (Original) The method of manufacturing a semiconductor device according to claim ~~9~~<sup>1</sup>, further comprising the step of forming a second insulation film on said conductive layer and said intrusion prevention film prior to said step of forming the first insulation film.

<sup>4</sup>  
Claim ~~12~~ (Original) The method of manufacturing a semiconductor device according to claim <sup>3</sup>~~1~~, wherein said second insulation film includes a film less hygroscopic than said first insulation film.

<sup>5</sup>  
Claim ~~13~~ (Original) The method of manufacturing a semiconductor device according to claim <sup>1</sup>~~9~~, further comprising the step of forming a third insulation film on said first insulation film after said step of implanting impurities into the first insulation film.

<sup>6</sup>  
Claim ~~14~~ (Currently Amended) The method of manufacturing a semiconductor device according to claim <sup>1</sup>~~9~~, wherein said first insulation film includes silicon oxide containing at least 1 atomic % of carbon.

<sup>7</sup>  
Claim ~~15~~ (Original) The method of manufacturing a semiconductor device according to claim <sup>1</sup>~~9~~, wherein said first insulation film includes an inorganic SOG film.

<sup>8</sup>  
Claim ~~16~~ (Original) The method of manufacturing a semiconductor device according to claim <sup>1</sup>~~9~~, wherein said step of introducing impurities is carried out by ion implantation.

<sup>9</sup>  
Claim ~~17~~ (Original) The method of manufacturing a semiconductor device according to claim <sup>1</sup>~~9~~, wherein said impurities include at least one element selected from the group consisting of argon, boron, nitrogen, and phosphorus.

Claim <sup>10</sup>~~18~~ (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a conductive layer on a substrate,

forming a film on said conductive layer, said film including at least one material selected from the group consisting of silicon oxide, silicon nitride, Ti, TiN, W, WN<sub>x</sub> and TiW, for substantially preventing impurities implanted from above of said conductive layer from intruding into said conductive layer,

*C' Incl.*  
patterning said conductive layer and said intrusion prevention film,

forming a first insulation film on said patterned conductive layer and intrusion prevention film, and

implanting the impurities into and penetrating through said first insulation film.

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